



A1 THRU A7

SURFACE MOUNT GENERAL PURPOSE SILICON RECTIFIER

Reverse Voltage - 50 to 1000 Volts Forward Current - 1.0 Ampere

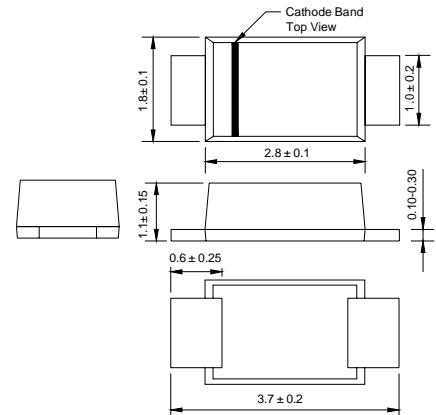
FEATURES

Glass passivated device
 Ideal for surface mounted applications
 Low reverse leakage
 Metallurgically bonded construction
 High temperature soldering guaranteed:
 250°C/10 seconds, 0.375" (9.5mm) lead length,
 5 lbs. (2.3kg) tension

MECHANICAL DATA

Case: JEDEC SOD-123FL molded plastic body over passivated chip
Terminals: Solderable per MIL-STD-750, Method 2026
Polarity: Color band denotes cathode end
Mounting Position: Any
Weight: 0.006 ounce, 0.02 grams

SOD-123FL



Dimensions in millimeters

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.
 Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

	SYMBOLS	A1	A2	A3	A4	A5	A6	A7	UNITS
Maximum repetitive peak reverse voltage	V_{RRM}	50	100	200	400	600	800	1000	VOLTS
Maximum RMS voltage	V_{RMS}	35	70	140	280	420	560	700	VOLTS
Maximum DC blocking voltage	V_{DC}	50	100	200	400	600	800	1000	VOLTS
Maximum average forward rectified current at $T_A=100^\circ\text{C}$ (NOTE 1)	$I_{(AV)}$	1.0							Amp
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method) $T_L=25^\circ\text{C}$	I_{FSM}	30.0							Amps
Maximum instantaneous forward voltage at 1.0A	V_F	1.0							Volts
Maximum DC reverse current $T_A=25^\circ\text{C}$ at rated DC blocking voltage $T_A=125^\circ\text{C}$	I_R	5.0 100.0							μA
Typical junction capacitance (NOTE 2)	C_J	4.0							pF
Typical thermal resistance (NOTE 3)	$R_{\theta JA}$	180							K/W
Operating junction and storage temperature range	T_J, T_{STG}	-55 to +150							$^\circ\text{C}$

- Note:** 1. Averaged over any 20ms period.
 2. Measured at 1MHz and applied reverse voltage of 4.0V D.C.
 3. Thermal resistance from junction to ambient at 0.375" (9.5mm) lead length, P.C.B. mounted



RATINGS AND CHARACTERISTIC CURVES A1 THRU A7

FIG.1 – TYPICAL FORWARD CHARACTERISTIC

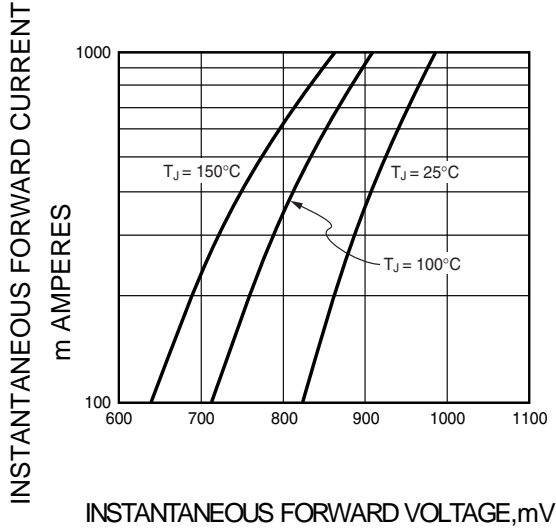


FIG.2 – TYPICAL JUNCTION CAPACITANCE

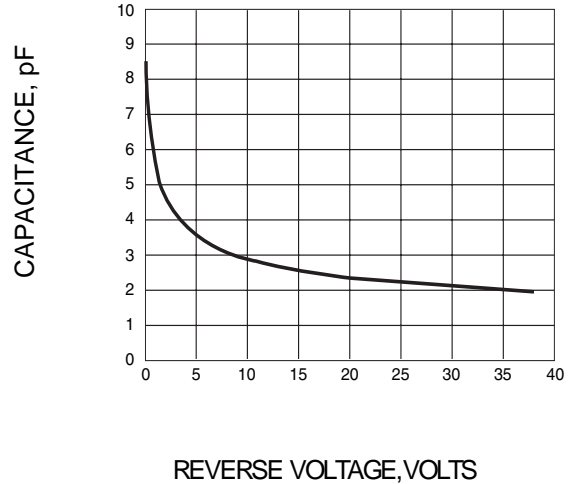


FIG.3 – TYPICAL INSTANTANEOUS REVERSE CHARACTERISTICS

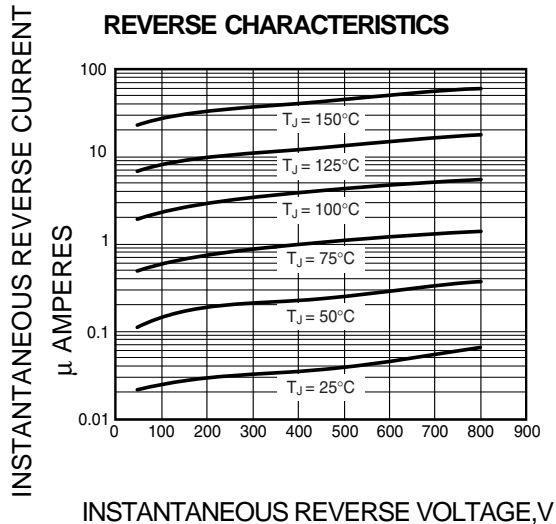
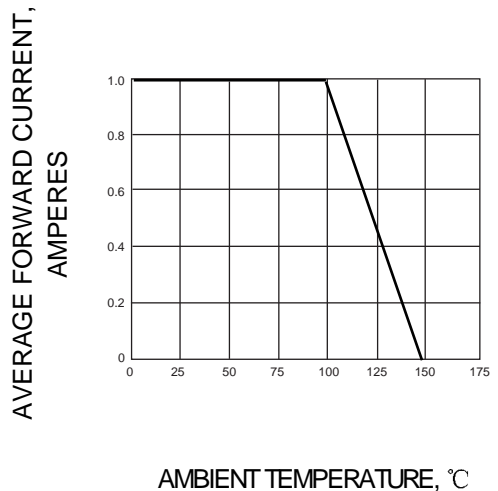


FIG.4 – FORWARD DERATING CURVE



单击下面可查看定价，库存，交付和生命周期等信息

[>>ZG\(中鑫半导体\)](#)